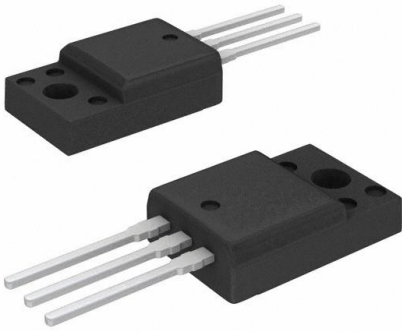


# FJPF9020TU Datasheet

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DiGi Electronics Part Number	FJPF9020TU-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	FJPF9020TU
Description	TRANS PNP DARL 550V 2A TO220F-3
Detailed Description	Bipolar (BJT) Transistor PNP - Darlington 550 V 2 A 15 W Through Hole TO-220F-3



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

FJPF9020TU

Series:

-

Transistor Type:

PNP - Darlington

Voltage - Collector Emitter Breakdown (Max):

550 V

Current - Collector Cutoff (Max):

100 $\mu$ A (ICBO)

Power - Max:

15 W

Operating Temperature:

150°C (TJ)

Package / Case:

TO-220-3 Full Pack

Base Product Number:

FJPF90

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

2 A

Vce Saturation (Max) @ Ib, Ic:

1.5V @ 20mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

400 @ 1A, 4V

Frequency - Transition:

-

Mounting Type:

Through Hole

Supplier Device Package:

TO-220F-3

## Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

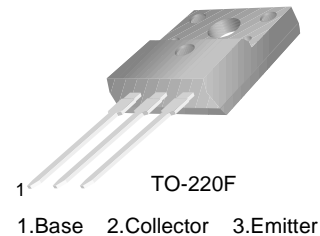
8541.29.0095



## FJPF9020

### Monolithic Construction With Built In Base-Emitter Shunt Resistors

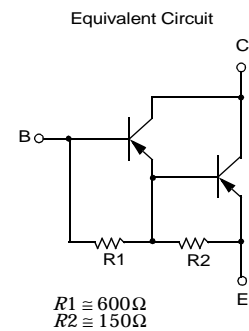
- High Collector-Base Breakdown Voltage :  $BV_{CBO} = -550V$
- High DC Current Gain :  $h_{FE} = 550$  @  $V_{CE} = -4V, I_C = -1A$  (Typ.)
- Industrial Use



### PNP Epitaxial Darlington Transistor

#### Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	- 550	V
$V_{CEO}$	Collector-Emitter Voltage	- 550	V
$V_{EBO}$	Emitter-Base Voltage	- 6	V
$I_C$	Collector Current (DC)	- 2	A
$I_{CP}$	Collector Current (Pulse)	- 4	A
$P_C$	Collector Dissipation ( $T_C=25^\circ C$ )	15	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ C$



#### Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -100\mu A, I_E = 0$	- 550			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -500\mu A, I_B = 0$	- 550			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -200mA, I_C = 0$	-6			V
$I_{CBO}$	Collector Cut-off Current	$V_{CE} = -550V, I_E = 0$			-100	$\mu A$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -6V, I_C = 0$		-10	-20	mA
$h_{FE}$	DC Current Gain	$V_{CE} = -4V, I_C = -1A$	400	550	700	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1A, I_B = -20mA$		-1.0	-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -1A, I_B = -20mA$		-1.5	-2.0	V

# Typical Characteristics

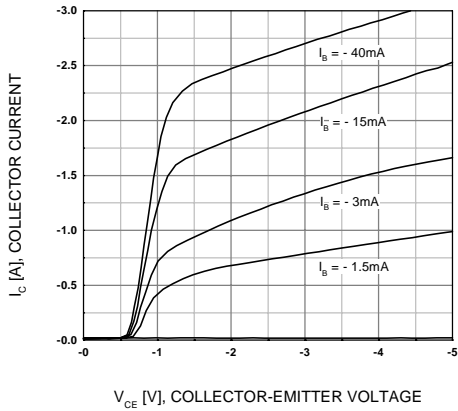


Figure 1. Static Characteristic

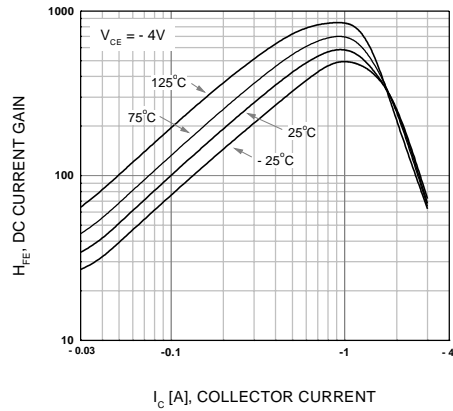


Figure 2. DC current Gain

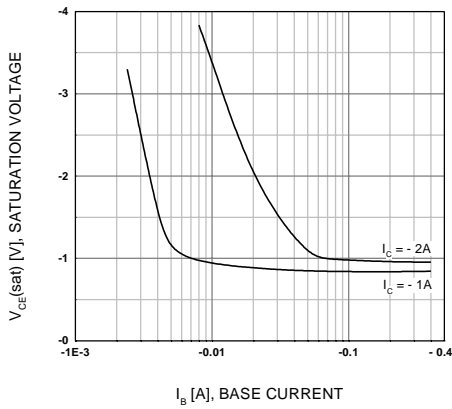


Figure 3.  $V_{CE(sat)}$  vs.  $I_b$  Characteristics

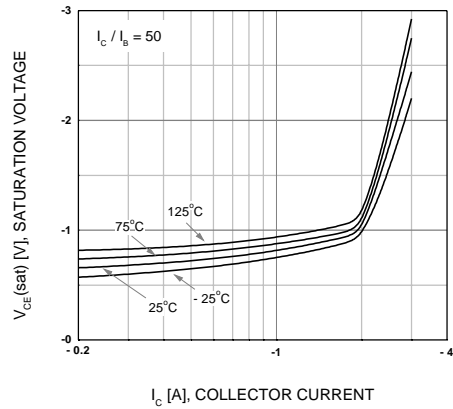


Figure 4. Collector-Emitter Saturation Voltage

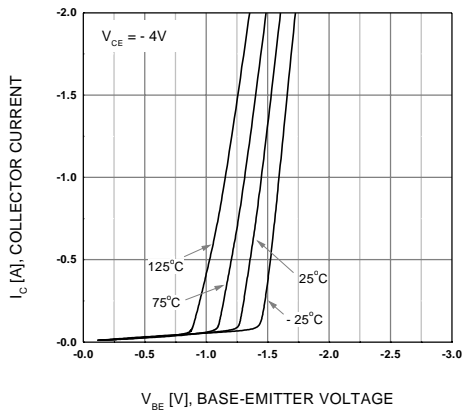


Figure 5. Base-Emitter On Voltage

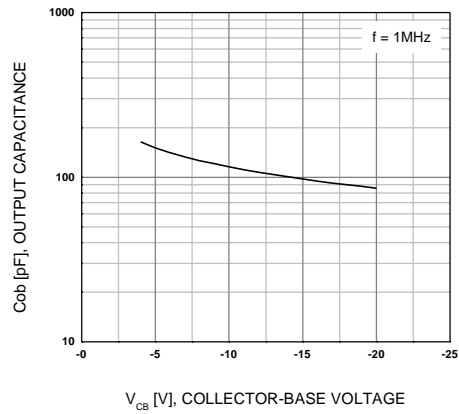
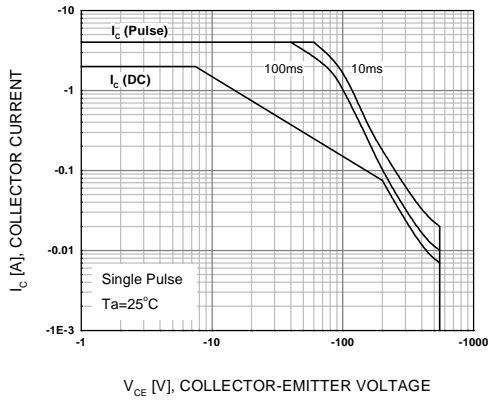
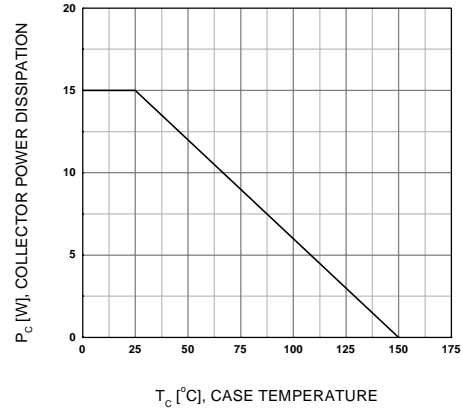


Figure 6. Output Capacitance

**Typical Characteristics** (Continued)



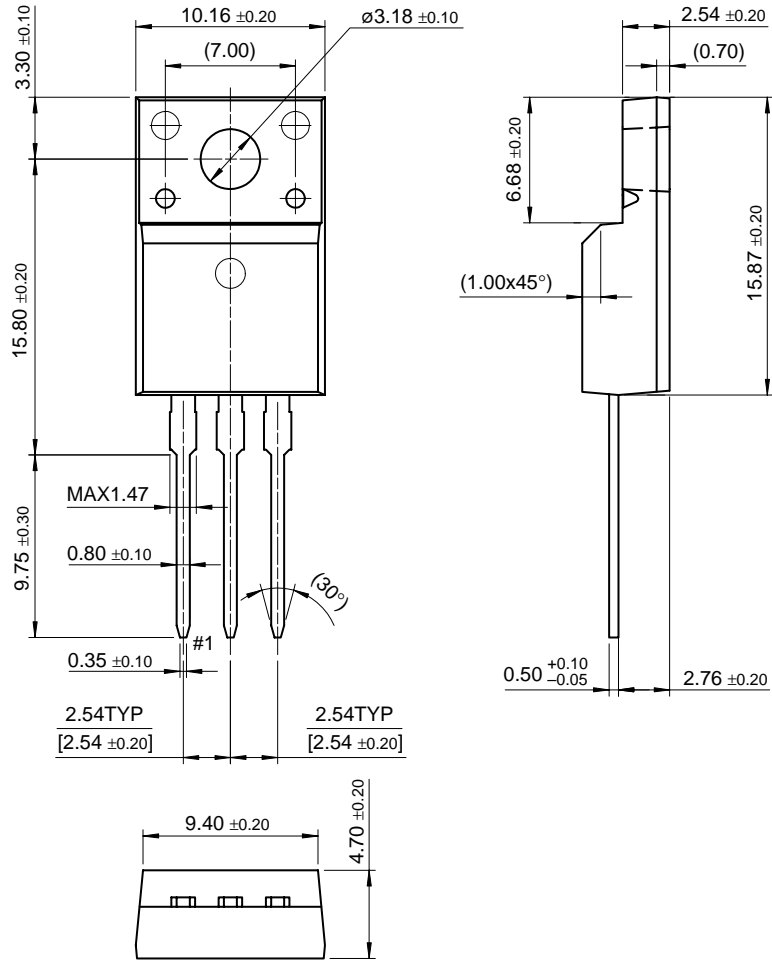
**Figure 7. Forward Bias Safe Operating Area**



**Figure 8. Power Derating**

Package Dimensions

TO-220F



Dimensions in Millimeters

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CROSSVOLT <sup>TM</sup>	GTO <sup>TM</sup>	POP <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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